

	Hits	Search Text	DBs
2	5	(non\$4volatile near12 memory near9 cell) and (IC or (integrat\$4 near9 circuit\$4)) and ((substrate or workpiece or wafer) same (dielectric or insulat\$4 or SiO or Si\$2N\$3) same (conductive or gate or (float\$4 near9 gate)) same (expos\$4 or etch\$4 or mask\$4)) and pedestal and ((word near9 line) or (conductive near5 line)) and (sidewall near9 spacer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
5	5	(non\$4volatile near22 memory near22 cell) and (IC or (integrat\$4 near9 circuit\$4)) and ((substrate or workpiece or wafer) same (dielectric or insulat\$4 or SiO or Si\$2N\$3) same (conductive or gate or (float\$4 near9 gate)) same (expos\$4 or etch\$4 or mask\$4 or pattern\$4)) and pedestal and ((word near9 line) or (conductive near5 line)) and (sidewall same spacer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
6	21	(IC or (integrat\$4 near9 circuit\$4)) and ((substrate or workpiece or wafer) same (dielectric or insulat\$4 or SiO or Si\$2N\$3) same (conductive or gate or (float\$4 near9 gate)) same (expos\$4 or etch\$4 or mask\$4 or pattern\$4)) and pedestal and ((word near9 line) or (conductive near5 line)) and (sidewall same spacer same dielectric) and ((dop\$4 or implant\$4) same (conductive or line))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
7	2	438/257.ccls. and (IC or (integrat\$4 near9 circuit\$4)) and ((substrate or workpiece or wafer) same (dielectric or insulat\$4 or SiO or Si\$2N\$3) same (conductive or gate or (float\$4 near9 gate)) same (expos\$4 or etch\$4 or mask\$4 or pattern\$4)) and pedestal and ((word near9 line) or (conductive near5 line)) and ((sidewall or spacer) same dielectric) and ((dop\$4 or implant\$4) same (conductive or line or word))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
8	3	438/257.ccls. and (IC or (integrat\$4 near9 circuit\$4)) and ((substrate or workpiece or wafer) same (dielectric or insulat\$4 or SiO or Si\$2N\$3) same (conductive or gate or (float\$4 near9 gate)) same (expos\$4 or etch\$4 or mask\$4 or pattern\$4)) and pedestal and ((word near9 line) or (conductive near5 line)) and ((sidewall or spacer) same dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
9	5	438/257.ccls. and (IC or (integrat\$4 near9 circuit\$4)) and ((substrate or workpiece or wafer) same (dielectric or insulat\$4 or SiO or Si\$2N\$3) same (conductive or gate or (float\$4 near9 gate)) same (expos\$4 or etch\$4 or mask\$4 or pattern\$4)) and ((word near9 line) or (conductive near5 line)) and ((sidewall or spacer) same dielectric) and (pedestal or (dummy near16 electrode) or (dummy near22 (structure or row)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
10	6	438/257.ccls. and (IC or (integrat\$4 near9 circuit\$4)) and ((substrate or workpiece or wafer) same (dielectric or insulat\$4 or SiO or Si\$2N\$3) same (conductive or gate or (float\$4 near9 gate))) and ((word near22 line) or (conductive near22 (pattern or line))) and ((sidewall or spacer) same dielectric) and (pedestal or (dummy near16 electrode) or (dummy near22 (structure or row or element)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
11	6	438/257.ccls. and (IC or (integrat\$4 near9 circuit\$4)) and ((substrate or workpiece or wafer) same (conductive or gate or (float\$4 near9 gate))) and ((word near22 line) or (conductive near22 (pattern or line))) and ((sidewall or spacer) same dielectric) and (pedestal or (dummy near16 electrode) or (dummy near22 (structure or row or element)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
12	531	438/257.ccls. and (IC or (integrat\$4 near9 circuit\$4)) and non\$4volatile and (memory near16 cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
13	214	438/257.ccls. and (IC or (integrat\$4 near9 circuit\$4)) and non\$4volatile and (memory near16 cell) and (word near12 line) and (conduct\$3 near16 (line or pattern or layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
14	106	438/257.ccls. and (IC or (integrat\$4 near9 circuit\$4)) and non\$4volatile and (memory near16 cell) and (word near12 line) and (conduct\$3 near16 (line or pattern or layer)) and spacer and (dielectric or insulat\$4) and sidewall	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB